Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit | |
|--|-----------------------------------|-------------|-------------|--|
| Collector – Emitter Voltage | V _{CEO} | -45 | Vdc | |
| Collector – Base Voltage | V _{CBO} | -50 | Vdc | |
| Emitter – Base Voltage | V _{EBO} | -5.0 | Vdc | |
| Collector Current – Continuous | Ic | -100 | mAdc | |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | P _D | 350 2.8 | mW mW/°C | |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 1.0 8.0 | W mW/°C | |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | °C | |

THERMAL CHARACTERISTICS

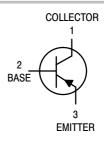
| Characteristic | Symbol | Max | Unit | |
|---|-----------------|-----|------|--|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 357 | °C/W | |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 125 | °C/W | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



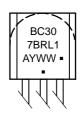
ON Semiconductor®

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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|------------|--------------------|-----------------------|
| BC307BRL1G | TO-92 (Pb-Free) | 2000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|----------------------|---------------|-------------------------|-------------------|------------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage (I _C = -2.0 mAdc, I _B = 0) | V _{(BR)CEO} | -45 | _ | _ | Vdc |
| Emitter – Base Breakdown Voltage (I _E = –100 μAdc, I _C = 0) | V _{(BR)EBO} | -5.0 | _ | - | Vdc |
| Collector–Emitter Leakage Current $(V_{CES} = -50 \text{ V}, V_{BE} = 0)$ $(V_{CES} = -50 \text{ V}, V_{BE} = 0) \text{ T}_A = 125^{\circ}\text{C}$ | I _{CES} | _ _ | -0.2 -0.2 | -15 -4.0 | nAdc μA |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain $ \begin{array}{l} (I_C = -10 \; \mu \text{Adc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ (I_C = -2.0 \; \text{mAdc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ (I_C = -100 \; \text{mAdc}, \; V_{CE} = -5.0 \; \text{Vdc}) \end{array} $ | h _{FE} | _ 200 _ | 150 290 180 | - 460 - | _ |
| | V _{CE(sat)} | - - - | -0.10 -0.30 -0.25 | -0.3 -0.6 - | Vdc |
| Base – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc) | V _{BE(sat)} | - - | -0.7 -1.0 | - - | Vdc |
| Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc) | V _{BE(on)} | -0.55 | -0.62 | -0.7 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | | |
| Current – Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –5.0 Vdc, f = 100 MHz) | f _T | _ | 280 | _ | MHz |
| Common Base Capacitance (V _{CB} = -10 Vdc, I _C = 0, f = 1.0 MHz) | C _{cbo} | _ | _ | 6.0 | pF |
| Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz) | NF | _ | 2.0 | 10 | dB |

^{1.} $I_C = -10$ mAdc on the constant base current characteristic, which yields the point $I_C = -11$ mAdc, $V_{CE} = -1.0$ V.

TYPICAL CHARACTERISTICS

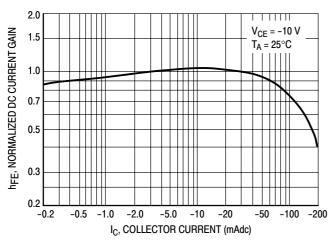


Figure 1. Normalized DC Current Gain

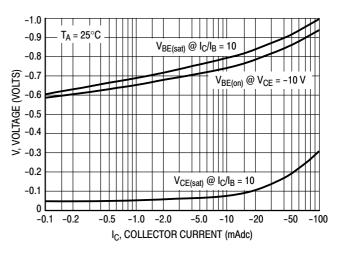


Figure 2. "Saturation" and "On" Voltages

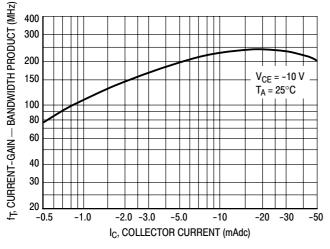


Figure 3. Current-Gain — Bandwidth Product

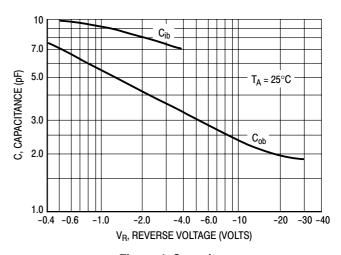


Figure 4. Capacitances

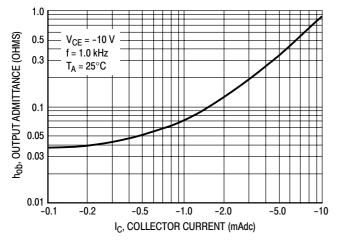


Figure 5. Output Admittance

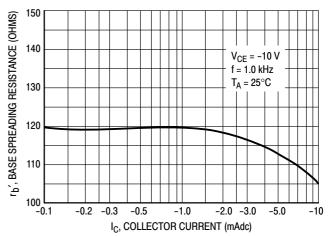
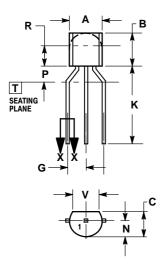


Figure 6. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**





NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | MILLIMETERS | | |
|-----|-------------|------|--|
| DIM | MIN MAX | | |
| Α | 4.45 | 5.20 | |
| В | 4.32 | 5.33 | |
| С | 3.18 | 4.19 | |
| D | 0.40 | 0.54 | |
| G | 2.40 | 2.80 | |
| J | 0.39 | 0.50 | |
| K | 12.70 | | |
| N | 2.04 | 2.66 | |
| P | 1.50 | 4.00 | |
| R | 2.93 | | |
| v | 3 43 | | |

STYLE 17:

PIN 1. COLLECTOR

BASE

3. EMITTER

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